Presenter	Institute	Title of Presentation
Session 1		
Beatriz Noheda	University of Groningen, Netherland	Operando studies of the interplay between ferroelectricity and electrochemistry in all-oxide MIM Hf_0.5Zr_0.5O_2 heterostructures
Nick Barrett	CEA-Saclay, Paris, France	Oxygen vacancies in hafnia-based ferroelectric capacitors
Martina Müller	Universität Konstanz, Germany	Defect and interface chemistry in ferroelectric HfO2 explored by HAXPES
Session 2		
P. Buragohain/A. Gruverman	UN Lincoln, Nebraska, USA	Nanoscale studies of imprint behavior in ferroelectric La:HfO2 capacitors
Alfred Kersch	Univ. of Appl. Sciences, Munich, Germany	Oxygen vacancies in HfO2/ZrO2 and impact on the formation of the ferroelectric phase
Lucian Pintilie	NIMP, Magurele, Romania	Structural investigations of HZO films and connection with macroscopic electrical properties
Session 3		
Sayeef Salahuddin	UC Berkeley, California, USA	Ferroelectricity and Negative Capacitance in Ultra-thin Layers of HfO2 Based Fluorite Oxides
F. Berg/U. Boettger	RWTH Aachen, Germany	Effects of Moisture in Ferroelectric Switching HfOx
E. Breyer/S. Slesazeck	Namlab, Dresden, Germany	Compact FeFET circuit building blocks for fast and efficient nonvolatile logic-in-memory
Session 4		
Min Hyuk Park	Pusan National University	Interfacial engineering as a strategy to improve remanent polarization of Hf0.5Zr0.5O2 thin film
Anna Chernikova/A. Markeev	MIPT, Moscow, Russia	Electrode-Ferroelectric Interface engineering for improvement of HfO2-based FeRAM memory stacks
Uwe Schroeder	Namlab, Dresden, Germany	Impact of interfacial layers on retention performance of Hf0.5Zr0.5O2 based capacitors
Session 5		
Laurent Grenouillet	LETI, Grenoble, France	HfO2-based BEOL-integrated ferroelectric capacitor for ultra low power FeRAM
Jordan Bouaziz/B. Vilquin	Université de Lyon, Lyon, France	Tracking polarization loss and imprint during electrical tests in sputtered TiN/HZO/TiN capacitors
Thanasis Dimoulas	Demokritos, Athens, Greece	Metastable ferroelectricity in scaled HZO induced by depolarizing fields: a phenomenological Landau-Ginzburg approach